OP550, OP552, OP555, OP560, OP565, OP750, OP770 Series

Electronics OP552

Features:

- · Wide receiving angle
- Four sensitivity ranges
- Side-looking package
- Ideal for space-limited applications
- Ideal for PCBoard mounting
- Choice of clear, opaque or blue-tinted package



Description:

OP550, OP552, OP555, OP750, and **OP770** series consists of a NPN silicon phototransistor molded in an epoxy package with a wide receiving angle that provides relatively even reception over a large area. The **OP750** and **OP770** have additional circuitry to enhance the operation of the device for stray light levels.

OP560 and **OP565** series consists of a NPN silicon photodarlington transistor molded in an epoxy package with a wide receiving angle that provides relatively even reception over a large area.

The side-looking package design allows easy PCBoard mounting of slotted optical switches or optical interrupt detectors.

The OP550, OP560, OP750 and OP770 devices have an external lens in a clear epoxy package.

The **OP552** device has an integral lens in an opaque plastic package that is optically transparent to infrared light but opaque to visible wavelengths. This feature allows the device to be used under high ambient light conditions—or anywhere external light sources could interfere with the intended sensing application (visible light immunity).

The **OP555** and **OP565** devices have an internal lens in a blue-tinted package. The lensing effect of this package allows an acceptance half-angle of 28° when measured from the optical axis to the half-power point.

These devices are 100% production tested using infrared light for close correlation with OPTEK's GaAs and GaAlAs emitters. All of these sensors are mechanically and spectrally matched to the **OP140, OP142, OP145, OP240** and **OP245** series of infrared emitting diodes.

<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.</u> For custom versions please contact your OPTEK representative.

Applications:

- Applications requiring wide receiving angle
- Applications requiring PCBoard mounting
- Space-limited applications
- Optical switches
- Optical interrupt detectors
- Optical encoders
- Non-contact position sensing
- Machine automation



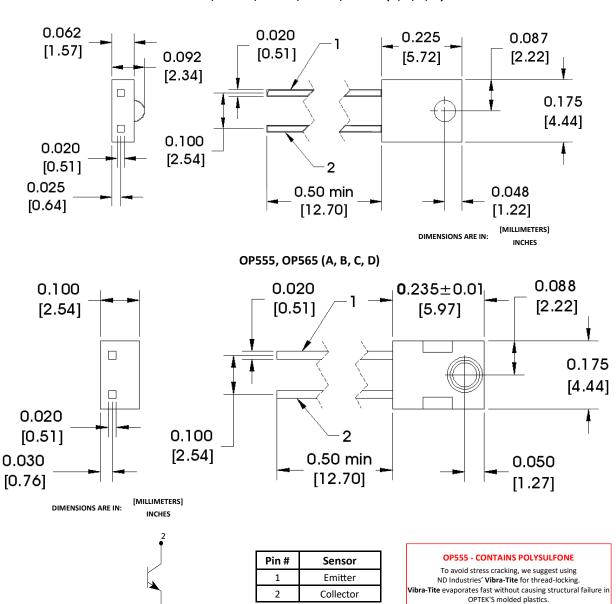
ОР	ГТ
55 = Phototransistor 56 = Photodarlington 75 = Phototransistor with R _{BE} 77 = Phototransistor with C _{CE}	A = Highest sensitivity level B = Sensitivity Level with Min. Max. C = Middle Sensitivity Level D = Lowest Sensitivity Level
	0 = Extended Lens - Clear Package 2 = Extended Lens - Blue Tinted Package 5 = Integral Lens - Blue Tinted Package

Available Part Numbers								
OP550A		OP555A	OP560A	_	OP750A		OP770A	
OP550B		OP555B		OP565B	OP750B			
OP550C	_	OP555C	OP560C					
OP550D	OP552D				OP750D			

OP550, OP552, OP555, OP560, OP565, OP750, OP770 Series



OP550, OP552, OP560, OP750, OP770 (A, B, C, D)



Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
- 2. For OP550, OP560, OP555 and OP565, derate linearly 1.33 mW/° C above 25° C. For OP552, derate linearly 1.25 mW/° C above 25° C.
- For all phototransistors in this series, the light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm. For OP550 and OP555 only, a radiometric intensity level that varies less than 10% over the entire lens surface of the phototransistor being tested applies.
- 4. To calculate typical collector dark current in μ A, use the formula $I_{CEO}=10^{\frac{(0.040\,T_A-3.4)}{A}}$, where T_A is ambient temperature in °C.

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Electrical Specifications

osolute Maximum Ratings (T _A = 25° C unless otherwise noted)		
Storage Temperature Range	-40° C to +100° C	
Operating Temperature Range		
OP550, OP555, OP560, OP565, OP750	-40° C to +100° C	
OP552	-40° C to +85° C	
Collector-Emitter Voltage		
OP550, OP552, OP555, OP560, OP750	30 V	
OP565	15 V	
Emitter-Collector Voltage	5 V	
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹	
Power Dissipation		
OP550, OP552, OP555, OP560, OP565	100 mW ⁽²	
OP750	200 mW ⁽²	





Electrical Specifications

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
	On-State Collector Current OP550A, OP555A OP550B, OP555B OP550C, OP555C OP550D, OP552D	2.55 1.30 0.25 0.25	- - -	- 4.70 2.40		$V_{CE} = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^{2(3)}$
	OP560A OP565B OP560C	6.6 3.3 1.1	- - -	- 9.8 -		$V_{CE} = 2.0 \text{ V}, E_E = 0.1 \text{ mW/cm}^{2(3)}$
I _{C(ON)}	OP750A 2.25 - 7.00 OP750B 1.50 - 4.20 OP750D 0.85 - 7.00	4.20	mA			
I _c /Δ T	OP770A	2.25	-	7.00		V _{CE} = 5.0 V, E _E = 1.0 mW/cm ²⁽³⁾
	Relative I _C Charge with Temperature	-	1.00	-	%/°C	$V_{CE} = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2, \lambda = 935 \text{ nr}$
I _{CEO}	Collector-Dark Current	-	-	100	nA	V _{CE} = 10.0 V, E _E = 0 ⁽⁴⁾
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OP550, OP552, OP555, OP750, OP770 OP560, OP565	30	-	-	V	$I_C = 100 \mu A, E_E = 0^{(4)}$ $I_C = 1 \text{ mA}, E_E = 0^{(4)}$
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	Ι _Ε = 100 μΑ
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OP550, OP552, OP555, OP750, OP770 OP560, OP565	-	-	0.40	V	$I_C = 100 \mu A, E_E = 1.0 \text{ mW/cm}^{2(3)}$ $I_C = 0.4 \text{ mA}, E_E = 0.1 \text{ mW/cm}^{2(3)}$

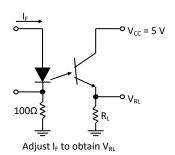
See page 2 for Notes

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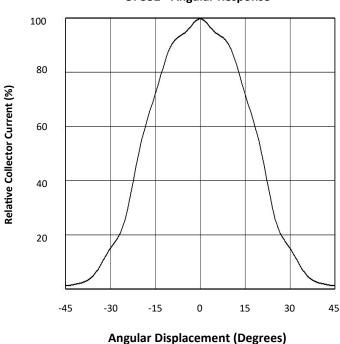


Performance

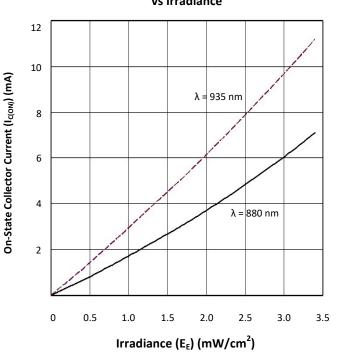
Switching Test Circuit



OP552 - Angular Response



OP552 - On-State Collector Current vs Irradiance



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Performance

OP552 - Output Vs Frequency

100

80

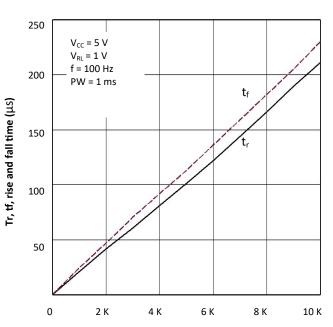
R_L = 10 K

R_L = 1 K

20

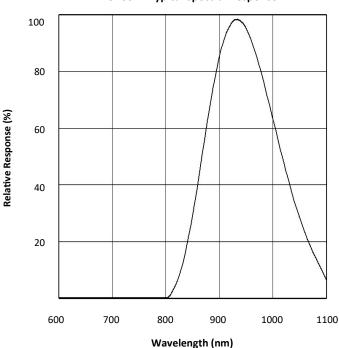
1 10 100 1000

OP552 - Rise and Fall Time vs Load Resistance



OP552 - Typical Spectral Response

Frequency (KHz)



Load Resistance (Ohms) OP552 - Coupling Characteristic

